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## N-Channel QFET<sup>®</sup> MOSFET 150 V, 90 A, 18 mΩ

#### Features

- $R_{DS(on)}$  = 18 m $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 45 A
- Low Gate Charge (Typ. 220 nC)
- Low Crss (Typ. 200 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Memperature Rating

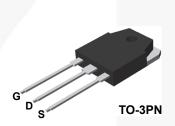
May 2014

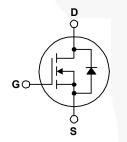
FQA90N15 — N-Channel QFET<sup>®</sup> MOSFET

## Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as audio amplifier, high efficiency switching for DC/DC converters, and DC motor control, uninterrupted power supply.





#### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		Parameter		FQA90N15	Unit	
V <sub>DSS</sub>	Drain-Source Voltage			150	V	
ID	Drain Current	- Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C		90 63.5	A A	
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	360	A	
V <sub>GSS</sub>	Gate-Source voltage			±25	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy		(Note 2)	1400	mJ	
I <sub>AR</sub>	Avalanche Current		(Note 1)	90	A	
E <sub>AR</sub>	Repetitive Avalanche Energy		(Note 1)	37.5	mJ	
dv/dt	Peak Diode Recove	ery dv/dt	(Note 3)	6.0	V/ns	
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C) - Derate Above 25°C			375 2.5	W W/°C	
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C		
Τ <sub>L</sub>	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		ose,	300	°C	

#### **Thermal Characteristics**

Symbol	Parameter	FQA90N15	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.4	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W	
$R_{\thetaJA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

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## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA90N15	FQA90N15	TO-3PN	Tube	N/A	N/A	30 units

### Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Conditions		Тур.	Max	Units
Off Charac	teristics				L	1
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	150			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, Referenced to 25°C		0.15		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	oltage Drain Current $V_{DS} = 150V, V_{GS} = 0V$ $V_{DS} = 120V, T_{C} = 150^{\circ}C$			1 10	μΑ μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward V <sub>GS</sub> = 25V, V <sub>DS</sub> = 0V				100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -25V, V <sub>DS</sub> = 0V			-100	nA
On Charac	teristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$			4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 45A		0.014	0.018	Ω
9 <sub>FS</sub>	Forward Transconductance $V_{DS} = 40V, I_D = 45A$			68		S
Dynamic C	haracteristics					
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz		6700	8700	pF
C <sub>oss</sub>	Output Capacitance			1400	1800	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			200	260	pF
Switching	Characteristics				•	
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 75V, I_D = 90A$ $R_G = 25\Omega$		105	220	ns
t <sub>r</sub>	Turn-On Rise Time			760	1500	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			470	950	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		410	830	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 120V, I <sub>D</sub> = 90A		220	285	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10V		43		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)	-	110		nC
Drain-Sour	rce Diode Characteristics and Maximur	n Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				90	А
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				360	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 90A			1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0V, I <sub>S</sub> = 90A		175		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> /dt =100A/μs		0.97		μC

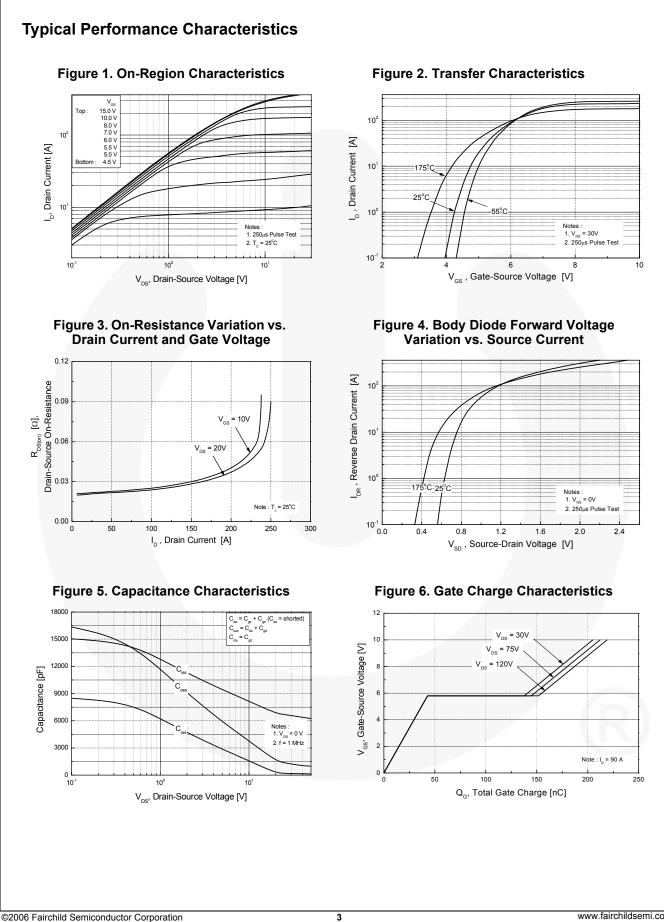
#### NOTES:

1. Repetitive rating: pulse-width limited by maximum junction temperature.

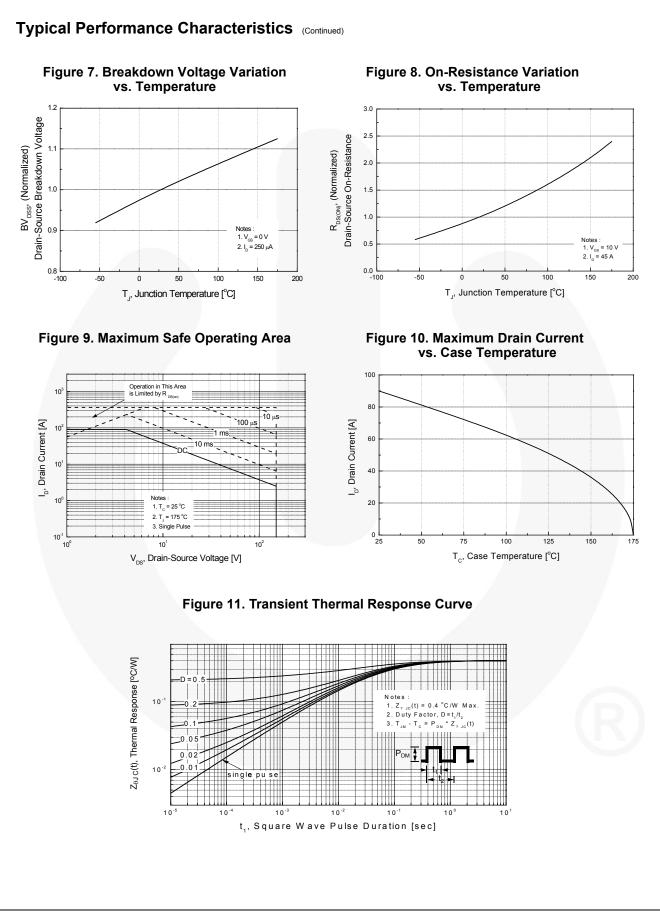
2. L = 0.29 mH, I\_{AS} = 90 A, V\_{DD} = 25 V, R\_G = 25  $\Omega,$  starting T\_J = 25°C.

 $3.I_{SD} \leq 90$  A, di/dt  $\leq 300$  A/µs,  $V_{DD} \leq BV_{DSS}$ , starting  $T_J$  = 25°C.

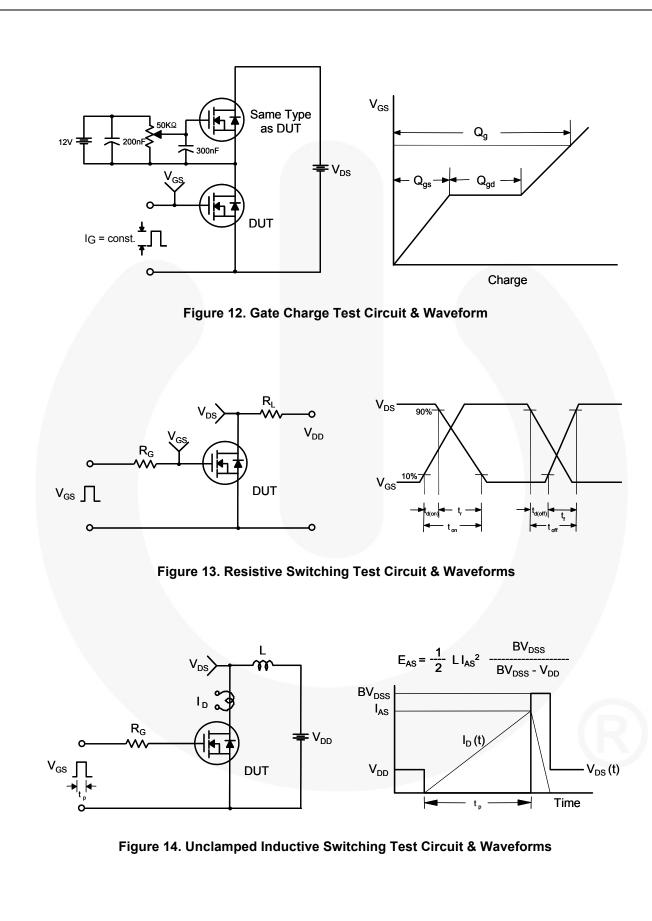
4. Essentially independent of operating temperature typical characteristics.



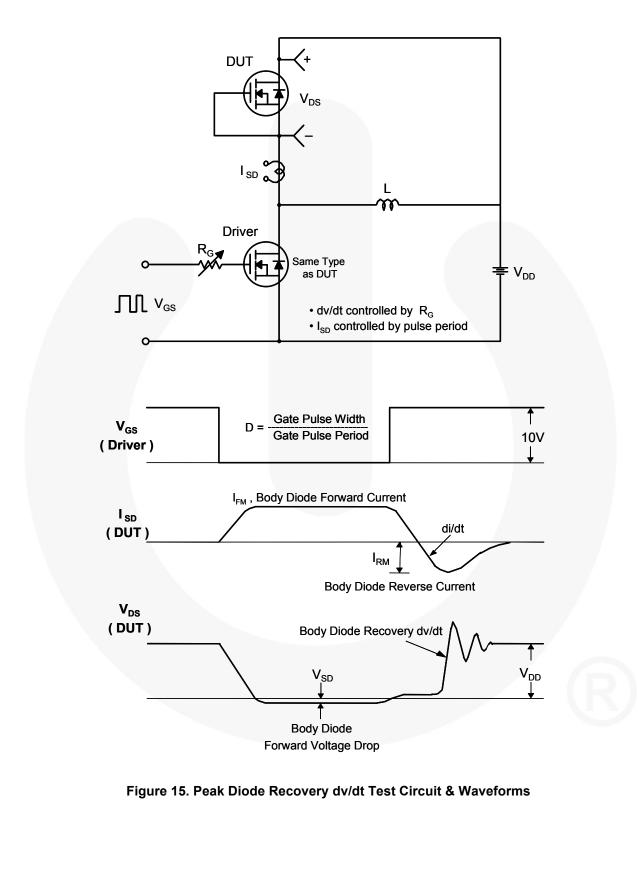
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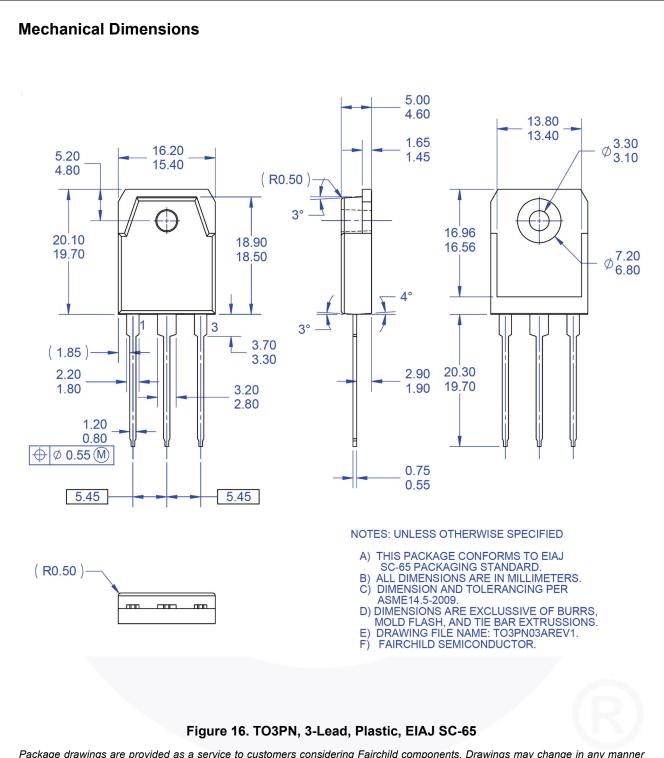


FQA90N15 — N-Channel QFET<sup>®</sup> MOSFET



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